

## CSIR-NET, GATE, SET, JEST, IIT-JAM, BARC, TIFR

Contact: 8830156303 | 8329503213

# Physical Science

# ELECTRONICS

Previous Year Questions [Topic-Wise]

With Answer Key

# **CSIR-NET/JRF, GATE, JEST, TIFR**

DPHYSICS KRISHNA CHOWK, NEW SANGAVI, PUNE-27 CONTACT: 8830156303

NO	TOPIC	PAGE NO:
	ANOLOG ELECTRONICS:	
1.	OP-AMP	1
2.	Network Theory & Circuit Analysis	19
3.	Diodes	25
4.	Bipolar Junction Transistor	32
5.	MOSFET, JFET	40
6.	Semiconductor	42
7.	Transient Circuit	45
8.	ADC & DAC	49
9.	Experimental Instruments Based Problems	51
10.	Wave Shaping	55
11.	Frequency Modulation	60
12.	Oscillatory	61
	DIGITAL ELECTRONICS:	
1.	Boolean Algebra	62
2.	Logic Gates	65
3.	Sequential	73
4.	Combinational Circuits	76
5.	Number System	78

# D PHYSICS

### ANALOG ELECTRONICS: OP-AMP

#### ✤ CSIR-NET PYQ

- **1.** A time varying signal  $V_{in}$  is fed to an op-amp circuit with output signal  $V_0$  as shown in the figure below.
  - The circuit implements a [CSIR-JUNE 2011] 10K



- (a) High pass filter with cutoff frequency 16 Hz.
- (b) High pass filter with cutoff frequency 100 Hz
- (c) Low pass filter with cutoff frequency <mark>1</mark>6 Hz

(d) Low pass filter with cutoff frequency 100 Hz.

**2.** In the operational amplifier circuit below, the voltage at point A is

[CSIR-DEC 2011]

(b) 0.5 V



(c) 0 V (d) -5.0 V

**3.** In the op-amp circuit shown in the figure below, the input voltage  $V_i$  is 1V. The value of the output  $V_0$  is **[CSIR-JUNE 2012]** 



(d) -0.25 V

4. In the op-amp circuit shown in the figure,  $V_i$  is a sinusoidal input signal of frequency 10 Hz and  $V_0$  is the output signal.



The magnitude of the gain and the phase shift, respectively, are close to the values

	[CSIR-DEC 2012]
and $\frac{\pi}{2}$	(b) $5\sqrt{2}$ and $\frac{-\pi}{2}$

(c) 10 and zero

(a)  $5\sqrt{2}$  a

(d) 10 and  $\pi$ 

5. Band-pass and band-reject filters can be implemented by combining a low pass and a high pass filter in series and in parallel, respectively. If the cut-off frequencies of the low pass and high pass filters are  $\omega_0^{LP}$  and  $\omega_0^{HP}$ , respectively, the condition required to implement the band-pass and band-reject filters are respectively.

[CSIR-DEC 2012]  
(a) 
$$\omega_0^{HP} < \omega_0^{LP}$$
 and  $\omega_0^{HP} < \omega_0^{LP}$   
(b)  $\omega_0^{HP} < \omega_0^{LP}$  and  $\omega_0^{HP} > \omega_0^{LP}$   
(c)  $\omega_0^{HP} > \omega_0^{LP}$  and  $\omega_0^{HP} < \omega_0^{LP}$ 

(d) 
$$\omega_0^{\text{HP}} > \omega_0^{\text{LP}}$$
 and  $\omega_0^{\text{HP}} > \omega_0^{\text{LP}}$ 

**6.** Consider the op-amp circuit shown in the figure.

If the input is a sinusoidal wave  $V_i = 5\sin(1000t)$ , then the amplitude of the output  $V_0$  is [CSIR-DEC 2013]



1

(a) 
$$\frac{5}{2}$$
 (b) 5

(c) $\frac{5\sqrt{2}}{2}$ (d) $5\sqrt{2}$
---

7. An op-amp based voltage follower
[CSIR-JUNE 2014]
(a) is useful for converting a low impedance source into a high impedance source

(b) is useful for converting a high impedance source into a low impedance source

(c) has infinitely high closed loop output impedance

(d) has infinitely high closed loop gain

**8.** Consider a Low Pass (LP) and a High Pass (HP) filter with cut-off frequencies  $f_{LP}$  and  $f_{HP}$  respectively, connected in series or in parallel configurations as shown in the Figures A and B below.

$(\Lambda)$	lnput	HP	LP	Output
(A)		$f_{HP}$	$f_{LP}$	



Which of the following statements is correct? [CSIR-DEC 2014]

(a) For  $f_{HP} < f_{LP}$ , A acts as a Band Pass filter and B acts as a Band Reject filter

(b) For  $f_{HP} > f_{Lp}$ , A stops the signal from passing through and B passes the signal without filtering

(c) For  $f_{HP} < f_{LP}$ , A acts as a Band Pass filter and B passes the signal without filtering

(d) For  $f_{HP} > f_{LP}$ , A passes the signal without filtering and B acts as a Band Reject filter

**9.** Consider the amplifier circuit comprising of the two op-amps  $A_1$  and  $A_2$  as shown in the figure If the input ac signal source has an impedance of

 $50k\Omega$ , which of the following statements is true?



(a)  $A_1$  is required in the circuit because the source impedance is much greater than r

(b)  $A_1$  is required in the circuit because the source impedance is much less than R

(c)  $A_1$  can be eliminated from the circuit without affecting the overall gain

(d)  $A_I$  is required in the circuit if the output has to follow the phase of the input signal

**10.** In the circuit given below, the thermistor has a resistance  $3k\Omega$  at 25°C. Its resistance decreases by  $150\Omega$  per °C upon heating. The output voltage of the circuit at 30°C is



**11.** If the parameters y and x are related by  $y = \log(x)$ , then the circuit that can be used to produce an output voltage  $V_0$  varying linearly with x is **[CSIR-DEC 2015]** 



**12.** In the circuit below, the input voltage  $V_i$  is 2 V,  $V_{cc} = 16 \text{ V}$ ,  $R_2 = 2 \text{k}\Omega$  and  $R_L = 10 \text{k}\Omega$ .



**18.** A circuit constructed using op-amp, resistor  $R_1 = 1k\Omega$  and capacitors  $C_1 = 1\mu F$  and  $C_2 = 0.1\mu F$ , is shown in the figure below.



This circuit will act as a (a) high pass filter

[CSIR-JUNE 2019] (b) low pass filter

- (c) band pass filter
- (d) band reject filter
- **19.** In the circuit diagram of a band pass filter shown below,  $R = 10k\Omega$ .



In order to get a lower cut-off frequency of 150 Hz and an upper cut-off frequency of 10kHz, the appropriate values of  $C_1$  and  $C_2$  respectively are [CSIR-DEC 2019] (a)  $0.1\mu$ F and 1.5nF (b)  $0.3\mu$ F and 5.0nF

- (c) 1.5nF and  $0.1\mu$ F
- (d) 5.0nF and  $0.3\mu$ F
- **20.** The I V characteristics of the diode D in the circuit below is given by

$$I = I_s \left( e^{\frac{qV}{k_B T}} - 1 \right)$$

where  $I_s$  is the reverse saturation current, V is



the voltage across the diode and T is the absolute temperature. If the input voltage is  $V_{in}$ , then the output voltage  $V_{out}$  is

[CSIR-JUNE 2020]

(a)
$$I_S R \ln\left(\frac{qV_{in}}{k_B T} + 1\right)$$
  
(b) $\frac{1}{q}k_B T \ln\left(\frac{q(V_{in} + I_S R)}{k_B T}\right)$ 

$$(c)\frac{1}{q}k_{B}T\ln\left(\frac{V_{in}}{I_{S}R}+1\right)$$
$$(d)-\frac{1}{q}k_{B}T\ln\left(\frac{V_{in}}{I_{S}R}+1\right)$$

**21.** In the circuit shown below, the gain of the opamp in the middle of its bandwidth is  $10^5$ . A sinusoidal voltage with angular frequency  $\omega = 100$  rad/s is applied to the input of the opamp.



The phase difference between the input andthe output voltage is[CSIR-JUNE 2020](a)  $5\pi/4$ (b)  $3\pi/4$ 

- (c)  $\pi/2$  (d)  $\pi$
- **22.** In the following circuit the input voltage  $V_{in}$  is such that  $|V_{in}| < |V_{out}|$ , where  $V_{sat}$  is the saturation voltage of the op-amp. (Assume that the diode is an ideal one and  $R_L C$  is much large than the duration of the measure



for the input voltage as shown in the figure above, the output voltage V<sub>out</sub> is best represented by [CSIR-JUNE 2021]



23. The pressure of a gas in a vessel needs be maintained between 1.5 bar to 2.5 bar in an experiment. The vessel is fitted with a pressure transducer that generates 4 mA to 20 mA current for pressure in the range 1 bar to 5 bar. The current output of the transducer has a linear dependence on the pressure.



The reference voltages  $V_1$  and  $V_2$  in the comparators in the circuit (shown in figure above) suitable for the desired operating conditions, are, respectively

(a) 2 V and 10 V

[CSIR-JUNE 2021] (b) 2 V and 5 V

(d) 3 V and 5 V

(c) 3 V and 10 V

24. In the circuit below, there is a voltage drop of 0.7 V across the diode in forward bias while no current flows through it in reverse bias.



In *V*<sub>in</sub> is a sinusoidal signal of frequency 50 Hz with rms value of 1 V the maximum current that flows through the diode is closest to
(a) 1*A*(b) 0.14 A

**25.** In the circuit shown below using an ideal op amp, inputs  $V_j$  (j = 1,2,3,4) may either be open or connected to a - 5 V battery.



The minimum measurement range of a voltmeter to measure all possible values of  $V_{out}$ 

ÎS	[CSIR-DEC 2023]
(a)10 V	(b)30 V
(c)3 V	(d)1 V

**26.** A circuit with operational amplifier is shown in the figure below.



The output voltage waveform V<sub>out</sub> will be closest to [CSIR-DEC 2023]







**27.** A train of square wave pulses is given to the input of an ideal opamp circuit shown below.



Given that the time period of the input pulses  $T \ll RC$  and the opamp does not get into saturation, which of the following best represents the output waveform?





**28.** Given the input voltage  $V_i$ , which of the following waveforms correctly represents the output voltage  $V_0$  in the circuit shown below ? [CSIR-JUNE 2016]





**29.** In the circuit shown below, the input voltage (in volts) is given by

$$V_{in}(t) = 0.1\sin(\omega_1 t) + \sin(\omega_2 t)$$

where 
$$\omega_1 = 5 \times 10^2 \text{ s}^{-1}$$
 and  $\omega_2 = 5 \times 10^4 \text{ s}^{-1}$ .



- The time varying part of the output voltage  $V_{out}(t)$  (in volts) is closest to **[CSIR DEC 2024]** (a)-0.2sin ( $\omega_1 t$ ) - 2sin ( $\omega_2 t$ )
  - (b) $-0.2\sin(\omega_1 t) + 0.2\cos(\omega_2 t)$
  - (c) $2\cos(\omega_1 t) + 0.2\cos(\omega_2 t)$
  - (d) $2\cos(\omega_1 t) 2\sin(\omega_2 t)$

#### ✤ GATE PYQ

1. The inverting input terminal of an operational amplifier (op-amp) is shorted with the output terminal apart from being grounded. A voltage signal  $v_i$  is applied to the non-inverting input terminal of the op-amp. Under this configuration, the op-amp functions as

[GATE 2004]

(a) an open loop inverter

- (b) a voltage to current converter
- (c) a voltage follower
- (d) an oscillator
- **2.** Figure shows a practical integrator with  $R_s = 30M\Omega$ ,  $R_F = 20M\Omega$  and  $C_F = 0.1\mu$ F. If a step (dc) voltage of +3 V is applied as input for  $0 \le t \le 4$  (t is in seconds), the output voltage is **[GATE 2004]**



- (a) a ramp function of -6 V
- (b) a step function of -12 V
- (c) a ramp function of -15 V
- (d) a ramp function of -4 V
- **3.** The output  $V_0$  of the ideal opamp circuit shown in the figure is [GATE 2005]



- (c) 5 V (d) 7 V
- **4.** The circuit shown in the figure can be used as a **[GATE 2005]**



- (a) high pass filter or a differentiator
- (b) high pass filter or an integrator

- (c) low pass filter or a differentiator
- (d) low pass filter or an integrator
- **5.** The low-pass active filter shown in the figure has a cut-off frequency of 2kHz and a pass band gainof 1.5. The values of the resistors are

[GATE 2006]



(a)  $R_1 = 10k\Omega; R_2 = 1.3\Omega$ 

(b)  $R_1 = 30k\Omega; R_2 = 1.3\Omega$ 

(c) 
$$R_1 = 10k\Omega; R_2 = 1.7\Omega$$

- (d)  $R_1 = 30k\Omega; R_2 = 1.7\Omega$
- **6.** In order to obtain a solution of the differential equation  $\frac{d^2v}{dt^2} 2\frac{dv}{dt} + v_1 = 0$ , involving voltages v(t) and  $v_1$ , an operational amplifier (Op-Amp) circuit would require at least [GATE 2006]

(a) two Op-Amp integrators and one Op-Amp adder

(b) two Op-Amp differentiators and one Op-Amp adder

(c) one Op-Amp integrator and one Op-Amp adder

(d) one Op-Amp integrator, one Op-Amp differentiator and one Op-Amp adder

 The circuit shown is based on ideal operational amplifiers. It acts as a [GATE 2007]









(d) Closed loop output impedance < Open loop output impedance

**26.** For the Op-Amp circuit shown below, choose the correct output waveform corresponding to the input  $V_{in} = 1.5 \sin 20\pi t$  (in Volts). The saturation voltage for this circuit is  $V_{sat} = \pm 10$  V.

[GATE 2022]  $V_{out}$  $V_{in}$ 20*k*Ω 2.2*k*Ω ≶ 10 5 (a)  $V_{\rm out}$  (volts) 0 -5Time 10 (b) 5  $V_{\rm out}$  (volts) 0 -5-10Time (c) 10 5  $V_{\rm out}$  (volts) 0 -5 -10



Time

27. An input voltage in the form of a square wave of frequency 1kHz is given to a circuit, which results in the output shown schematically below. Which one of the following options is the CORRECT representation of the circuit?

[GATE 2023]





The output voltage  $V_0$  is V (integer).

**29.** The figure shows an opamp circuit with a 5.1 V Zener diode in the feedback loop. The opamp runs from  $\pm 15$  V supplies. If a  $\pm 1$  V signal is applied at the input, the output voltage (rounded off to one decimal place) is

[GATE 2025]



#### ✤ JEST PYQ

**1.** A capacitor C is connected to a battery  $V_0$  through three equal resistors R and a switch S as shown below:



The capacitor is initially uncharged. At time t = 0, the switch *S* is closed. The voltage across the capacitor as a function of time ' *t* ' for t > 0 is given by [JEST 2012]

- (a)  $(V_0/2)(1 \exp(-t/2Rc))$
- (b)  $(V_0/3)(1 \exp(-t/3Rc))$
- (c)  $(V_0/3)(1 \exp(-3t/2Rc))$
- (d)  $(V_0/2)(1 \exp(-2t/3Rc))$
- **2.** The classic three op-amp instrumentation amplifier configuration is shown below:



The op-amp are ideal and all resistors are of equal value R. The gain, defined as the output voltage  $V_0$  divided by the differential input voltage  $V_1 - V_2$ , is equal to [JEST 2012] (a) 2 (b) 3

**3.** What is the voltage at the output of the following operational amplifier circuit [see figure 1]?

(d) 6

[JEST 2015]



- (c)  $1\mu V$  (d) 1Nv
- **4.** Consider a 741 operational amplifier circuit as shown below, where  $V_{CC} = V_{EE} = +15V$  and  $R = 2.2k\Omega$ . If  $V_1 = 2$ mV, what is the value of V<sub>0</sub> with respect to the ground? **[JEST 2017]**



5. Analysis the ideal op-amp circuit in the figure. Which one of the following statements is true about the output voltage V<sub>out</sub>, when terminal '*C* ' is connected to point '*A* ' and then to point '*B* '? [JEST 2019]



 $(a)V_{\text{out}} = V_{\text{in}} \text{ and } V_{\text{out}} = -V_{\text{in}} \text{ when '} C \text{ ' is}$ (a) +40mV(b) -40*mV* connected to ' A ' and ' B ', respectively (c) +20*mV* (d) -20mV(b)  $V_{\text{out}} = -V_{\text{in}}$  and  $V_{\text{out}} = V_{\text{in}}$  when 'C' is connected to ' A ' and ' B ', respectively 9. What is the output voltage of the following circuit for the input current 1nA? [JEST 2022] (c)  $V_{\text{out}} = -V_{\text{in}}$  when '*C* ' is connected to 10 MΩ  $\sim$ either 'A' or 'B' (d)  $V_{\text{out}} = V_{\text{in}}$  when '*C* ' is connected to either ' A' or 'B'l kΩ 6. Analyse the op-amp circuit shown in the figure  $99 \ k\Omega$ below. What is the output voltage  $(V_0)$  in millivolts if  $V_1 = 2.5$  and  $V_2 = 2.25$  V? (a) 1mV (b) 1 V (c) 1µV (d) 1Nv  $5 k\Omega$  $\geq 5 k\Omega$ -10V**10.** Consider the Op-Amp differentiator presented  $5 k\Omega$ +10V in Figure (a). Take  $C = 0.002 \mu$ F and  $R_f = 2 \text{ k}\Omega$ . 500Ω <sup><</sup> For a triangular wave input shown in the figure **↓**\_10*V*  $5 k\Omega$ [JEST 2023] (b), 5 kΩ +10V $\leq 5 k\Omega$ 7. An ideal op-amp and a silicon transistor *T* are used in the following circuit. Find the output b) voltage V<sub>out</sub> [JEST 2021] determine the output voltage waveform. +15VV<sub>out</sub>  $\sim$ +8V  $2k\Omega$ -15V10µs 15µs 20µs 5µs t -8V (a) +5.3 V (b) -0.7 V (a) (c) + 0.7 V(d) - 15 V+4 **8.** In the figure below with ideal op-amps, the value of R = 10k $\Omega$ ,  $V_1 = -10$ mV, and  $V_2 =$ 10µs 15µs 20µs 5µs t -30mV. -4\ [JEST 2021] Calculate V<sub>out</sub>. Calculate  $V_{out}$ . *R* www. R MMM-(b) R MMW







2

2 3 4 5



**5.** In the generalized operational amplifier circuit shown on the right, the op. amp. has a very high input impedance ( $Z > 50M\Omega$ ) and an open gain of 1000 for the frequency range under consideration. Assuming that the op. amp. draws negligible current, the voltage ratio  $V_2/V_1$  is approximately [TIFR 2016]



6. For the circuit depicted on the right, the input voltage  $V_i$  is a simple sinusoid as shown below, where the time period is much smaller compared to the time constant of this circuit.







The voltage  $V_o$  across *C* is best represented by



**7.** The following circuit is fed with an input sine wave of frequency 50 Hz.



Which of the following graphs (solid line is input and dashed line is output) best represents the correct situation?





8. The figure below shows an unknown circuit, with an input and output voltage signal.



From the form of the input and output signals, one can infer that the circuit is likely to be [TIFR 2018]





For the parameters indicated in the figure, the ratio of the maximum voltage at  $V_{out}$  to the maximum voltage at  $V_c$  is [TIFR 2020] (a) 1/8 (b) 1/7

(c) 2/7 (d) 1/4

14. An operational amplifier is configured as shown in the figure below. For an AC input this circuit behaves effectively as [TIFR 2021]



- (a) a resistor with a negative resistance.
- (b) an inductor with a negative inductance.
- (c) a capacitor with a negative capacitance.
- (d) an inductor with a positive inductance
- **15.** Consider the following circuit with an op-amp.



If the output voltage  $V_0$  is measured to be  $V_0 = -V$ , then the value of the feedback resistance  $R_f$  must be [TIFR 2021] (a) $R_f = nR$ 

(b) 
$$R_f = \frac{3R}{n(n+1)(2n+1)}$$

(c) 
$$R_f = \frac{6R}{n(n+1)(2n+1)}$$

- (d)  $R_f = R/n$
- **16.** Consider a circuit with an operational amplifier (op amp) and four resistors as sketched below.



**17.** The non-inverting amplifier shown in the figure on the right is constructed using a nonideal operational amplified (op amp) with a finite open loop gain *A*.

The value of feedback fraction is

$$B = \frac{R_2}{R_1 + R_2} = 0.1$$

If the gain *A* varies such that  $10^4 < A < 10^5$ 

then the approximate percentage variation in



the closed loop gain will b	e. <b>[TIFR 2022]</b>
(a) 0.09%	(b) 0.0%

- (c) 0.9% (d) 9.0%
- **18.** At what value of  $R_f$  will the ideal op-amp shown in the figure provide a gain of 6? **[TIFR 2023]**



**19.** For the circuit on the right, which graph<br/>represents  $V_{out}$  correctly for the  $V_{in}$  shown<br/>below?**[TIFR 2025]** 











	A	nswers key	/	
		CSIR-NET		
1. a	2. a	3. c	4. d	5. b
6. c	7. b	8. a	9. a	10. c
11. с	12. c	13. d	14. d	15. b
16. c	17. b	18. a	19. a	20. d
21. a	22. a	23. d	24. с	25. a
26. a	27. d	28. b	29. b	
		GATE		
1. c	2. d	3. a	4. d	5. d
6. a	7. b	8. c	9. d	10. b
11. c	12. a	13. a	14. d	15. a
16. b	17. a	18. b	19. b	20. c
21. 1	223.6	23. с	24. с	25. acd
26. a	27. a	2812	29.	
		JEST		
1. d	2. b	3. b	4. c	5. a
6. 5250	7. b	8. c	9. b	10. a
11. d				
		TIFR		
1. b	2. c	3. a	4. d	5. c
6. c	7. c	8. b	9. a	10. b
11. b	12. a	13. a	14. c	15. c
16. c	17. с	18. c	19. a	

### ANALOG ELECTRONICS: Network Theory & Circuit Analysis

 A resistance is measured by passing current through it and measuring the resulting voltage drop. If the voltmeter and the ammeter have uncertainties of 3% and 4%, respectively, then (A) The uncertainty in the value of resistance is

[CSIR-JUNE 2011] (b) 3.5%

(a) 7.0%

(c) 5.0% (d) 12.0%

(B) The uncertainty in the computed value of the power dissipated in resistance is(a) 7% (b) 5%

- (c) 11% (d) 9%
- **2.** A battery powers two circuits  $C_1$  and  $C_2$  as shown in t the figure



The total current I drawn from the battery is estimated by measuring the currents  $I_1$  and  $I_2$ through the individual circuits. If  $I_1$  and  $I_2$  are both 200 mA and if the errors in their measurement are 3 mA and 4 mA respectively, the error in the estimate of 1 is:

(a) 7.0 mA

(c) 5.0 mA

**[CSIR-DEC 2011]** (b) 7.5 Ma

(d) 10.5 mA

**3.** The insulation resistance R of an insulated cable is measured by connecting it in parallel with a capacitor C, a voltmeter, and battery B as shown. The voltage across the cable dropped from 150 V to 15 V, 1000 seconds after the switch S is closed. If the capacitance of the cable is  $5\mu$ F then its insulation resistance is



|--|

**4.** An ac signal of the type as shown in the figure, is applied across a resistor  $R = 1\Omega$ .



The power dissipated across the resistor is [CSIR-JUNE 2019]

(a) 12.5 W

(c) 25 W

(d) 21.5 W

(b) 9 W

(d)  $10^{6}\Omega$ 

**5.** Two voltmeters *A* and *B* with internal resistances  $2M\Omega$  and  $0.1k\Omega$  are used to measure the voltage drops  $V_A$  and  $V_B$ , respectively, across the resistor *R* in the circuit shown below.

The ratio  $V_A/V_B$  is (a) 0.58

(c) 1

[CSIR-JUNE 2020] (b) 1.73

(d) 2

6. An inductor *L*, a capacitor *C* and a resistor *R* are connected in series to an *AC* source,  $V = V_0 \sin \omega t$ . If the net current is found to depend only on *R*, then [CSIR-NOV 2020] (a) C = 0 (b) L = 0

(c)
$$\omega = 1/\sqrt{LC}$$
 (d)  $\omega = \sqrt{\frac{1}{LC} - \frac{R^2}{4L^2}}$ 

**7.** A circuit needs to be designed to measure the resistance *R* of a cylinder *PQ* to the best possible accuracy, using an ammeter *A*, a voltmeter *V*, a battery *E* and a current source  $I_S$  (all assumed to be ideal). The value of *R* is known to be approximately  $10\Omega$ , and the resistance *W* of each of the connecting wires is

close to  $10\Omega$ . If the current from the current source and voltage from the battery are known exactly, which of the following circuits provides the most accurate measurement of *R* ?



#### (c) C

(d) *A* 

8. A train of impulses of frequency 500 Hz, in which the temporal width of each spike is negligible compared to its period, is used to sample a sinusoidal input signal of frequency 100 Hz. The sampled output is

#### [CSIR-JUNE 2023]

(a) Discrete with the spacing between the peaks being the same as the time period of the sampling signal

(b) a sinusoidal wave with the same time period as the sampling signal

(c) discrete with the spacing between the peaks being the same as the time period of the input signal

(d) a sinusoidal wave with the same time period as the input signal

**9.** In the circuit shown in the figure, the resistances *R* and *R'* change due to strain. While *R* increases, *R'* decreases by the same amount  $\Delta R$  due to the applied strain. The unstrained values of *R* and *R'* are 100 $\Omega$  each. If same strain is applied to all the resistors, and the output voltage (*V*<sub>ab</sub>) changes to 0.3 V, then  $\Delta R$  is closest to

[CSIR JUNE 2024]



10. A battery with an open circuit voltage of 10 V is connected to a load resistor of  $485\Omega$  and the voltage measured across the battery terminals using an ideal voltmeter is 9.7 V. The internal resistance of the battery is closest to

**[CSIR JUNE 2024]** (b)15Ω

(c)20Ω

(a)30Ω

(d)40Ω

**11.** A circuit component consists of a resistor in parallel with an ideal current source. The I - V characteristics of the component was measured using a variable voltage source and an ammeter 'A'.



The arrow in the figure indicates the positive direction of current. The I-V characteristics of the component is best represented by

[CSIR DEC 2024]





#### ✤ GATE PYQ

**1.** A resistance of  $600\Omega$  is parallel to an inductance of reactance  $600(\Omega)$  applied voltage, then the total impedance of the circuit is

	[GATE 2001]
(a) 628Ω	(b) 268Ω

- (c)  $424\Omega$  (d)  $300\Omega$
- 2. In the circuit shown in the figure the Thevenin voltage  $V_{Th}$  and Thevenin resistance  $R_{Th}$  as seen by the load resistance  $R_L$  (= 1 $k\Omega$ ) are respectively [GATE 2005]



(c) 20 V, 2kΩ

- (d) 10 V, 5Kω
- For the circuit shown, the potential difference (in Volts) across R<sub>L</sub> is [GATE 2007]



**4.** An a. c. voltage of 220  $V_{ms}$  is applied to the primary of a 10:1 step-down transformer. The secondary of the transformer is centre lapped and connected to a full wave rectifier with a load resistance. The d. c. voltage appearing across the load is

(a) 
$$\frac{22}{\pi}$$
 (b)  $\frac{31}{\pi}$   
(c)  $\frac{62}{\pi}$  (d)  $\frac{44}{\pi}$ 

 Let I<sub>1</sub> and I<sub>2</sub> represent mesh currents in the loop abcda and befcb respectively. The correct expression describing Kirchoff's voltage loop law in one of the following loop is [GATE 2008]



voltage source and a dc current source with internal resistances  $R_1$  and  $R_2$ , respectively, are equal. The product  $R_1R_2$  in units of ohm <sup>2</sup> (rounded off to one decimal place) is

#### [GATE 2019]

7. A power supply has internal resistance  $R_S$  and open load voltage  $V_S = 5$  V. When a load resistance  $R_L$  is connected to the power supply, a voltage drop of  $V_L = 4V$  is measured across the load. The value of  $\frac{R_L}{R_S}$  is (Round off to the nearest integer) [GATE 2022]

#### ✤ JEST PYQ

**1.** The ratio of maximum to minimum resistance that can be obtained with  $N1 - \Omega$  resistors is **[JEST 2012]** 

(a) N

(b) N<sup>2</sup>

- (c) 1  $(d) \infty$
- 2. The temperature of a thin bulb filament (assuming that the resistance of the filament is nearly constant) of radius ' r ' and length L is proportional to [JEST 2014] (a)  $r^{1/4}L^{-1/2}$  (b)  $L^2r$

(c)  $r^{1/4}L^{-1}$  (d)  $r^2L^{-1}$ 

**3.** It is found that when the resistance *R* indicated in the figure below is changed from  $1k\Omega$  to  $10k\Omega$ , the current flowing through the resistance *R'* does not change. What is the





8. If a resistor of  $10k\Omega$  and a capacitor of  $0.5\mu$  F are connected in series across an AC supply of 220 V (rms) at 50 Hz , what is the average power (in mW , to the nearest integer) dissipated in the circuit? [JEST 2025]

#### TIFR PYQ

1. n the circuit given below, a person measures 9.0 V across the battery, 3.0 V across the  $2M\Omega$  resistor  $R_A$  and 4.5 V across the unknown resistor  $R_B$ , using an ordinary voltmeter which has a finite input resistance r. Assuming that the battery has negligible internal resistance, it follows that (i) the resistance  $R_B$  and (ii) the input resistance r of the voltmeter are, in  $M\Omega$ ,





2. The current read by the ammeter (A) in the circuit given below is [TIFR 2011]



(b) 100.0 mA

(c) 54.5 mA

**3.** You are given the following circuit and two instruments: a voltmeter and an ammeter both with 0.001% accuracy in their readings.



Which of the following methods will result in the most accurate reading for the current without interrupting the current in the circuit? [TIFR 2014]

(a) Use voltmeter to measure voltage across points B and C

(b) Use the ammeter to measure current at point B

(c) Use voltmeter to measure voltage across points A and B □

(d) Use voltmeter to measure voltage across points A and C

**4.** A student in the laboratory is provided with a bunch of standard resistors as well as the following instruments

----Voltmeter accurate to 0.1 V

---Thermometer accurate to 0.1C

- ----Ammeter accurate to 0.01 A
- ---Stop watch accurate to 0.05 s

----Constant current source (ideal)

---Constant voltage source (ideal)

Using this equipment (and nothing else), the student is expected to measure the resistance *R* of one of the given resistors. The least accurate result would be obtained by [TIFR 2016] (a) measuring the Joule heating.

(b) passing a constant current and measuring the voltage across it.

(c) measuring the current on application of a constant voltage across it.

(d) the Wheatstone bridge method.

**5.** The circuit shown below contains an unknown device *X*.



The current-voltage characteristics of the device X were determined and are shown in the plot given below. [TIFR 2016]



Determine the current *I* (in mA) flowing through the device X.

**6.** A realistic voltmeter can be modelled as an ideal voltmeter with an input resistor in parallel as shown below:



- Such a realistic voltmeter, with input resistance  $1k\Omega$ , gives a reading of 100 mV when connected to a voltage source with source resistance  $50\Omega$ . What will a similar voltmeter, with input resistance  $1M\Omega$ , read in mV, when connected to the same voltage source?] [TIFR 2018]
- **7.** The current *i* flowing through the following circuit is



(a) 0.5 A

(c) 0.75 A (d) 1.0 A

**8.** Consider the circuit shown on the right, which involves an op-amp and two resistors, with an input voltage marked INPUT.

Which of the following circuit components, when connected across the input terminals, is most likely to create a problem in the normal operation of the circuit? **[TIFR 2018]** 



(a) A voltage source with very high Thevenin resistance.

(b) A current source with a very high Nor<mark>t</mark>on resistance.

(c) A voltage source with a very low Thevenin resistance.

(d) A current source with a very low Norton resistance.

**9.** A badly-designed voltmeter is modelled as an ideal voltmeter with a large resistor (R) and a large capacitor (C) connected in parallel to it. Given this information, which of the following statements describes what happens when this voltmeter is connected to a DC voltage source with voltage V and internal resistance  $r(r \ll R)$ ? [TIFR 2020]

(a) The reading on the voltmeter rises slowly and becomes steady at a value slightly less than *V*.

(b) The reading on the voltmeter starts at a value slightly less than *V* and slowly falls to zero.

(c) The reading on the voltmeter rises slowly to a maximum value close to *V* and then slowly goes to zero.

(d) The reading on the voltmeter reads zero even when connected to the voltage source.

10. In an amplifier circuit, an input sine wave of amplitude 5 V gives a sine wave of amplitude 25 V as an output in an open load configuration. On applying a 20kΩ load resistance, the output drops to 10 V. This implies that the output resistance of the amplifier must be

[TIFR 2021]

- (a)  $2k\Omega$  (b)  $20k\Omega$
- (c)  $10k\Omega$  (d)  $30k\Omega$
- **11.** It is required to design a circuit with an impedance  $Z(\omega)$  such that  $Z(\omega) = ik(\omega \omega_0)$  for a range of frequencies  $\omega$  such that  $|\omega \omega_0|/\omega_0 \ll 1$  where k and  $\omega_0$  are constant real numbers.



		(a)	• •—		2_	<b> </b> 0	(b)	<u>م</u>	77777	n
		(c) O	-		<u> </u>	~	(d)	o		
				*	An	swer l	Key			
					CSI	R-NET				
	1.	b/b	2.	С	3.	b	4.	d	5.	b
4	6.	С	7.	b	8.	а	9.	а	10.	b
M	11.	b								
GATE										
	1.	b	2.	а	3.	а	4.	d	5.	a
	6.	22.09	7.	4						
JEST PYQ										
	1.	b	2.	d	3.	b	4.	0016	5.	b
	6.	С	7.	b	8.	3444				
					TIF	'R PYQ				
	1.		2.		3.	С	4.	а	5.	012
	6.	105	7.	С	8.	С	9.	а	10.	d
	11.	а								

### **ANALOG ELECTRONICS: Diodes**

345 t(s)

2 3 4 5 6

t(s)

#### ✤ CSIR-NET PYQ

 The figure below shows a voltage regulator utilizing a Zener diode of breakdown voltage 5 V and a positive triangular wave input of amplitude 10 V.



For  $V_i > 5$  V, the Zener regulates the output voltage by channeling the excess current through it self. Which of the following waveforms shows the current '*i*' passing through the Zener diode? **[CSIR-DEC 2011]** 



**2.** A diode D as shown in the circuit as an i - v relation which can be proximated by



The value of  $v_D$  in the circuit is:

(a)  $(-1 + \sqrt{11})V$  (b) 8 V

- (c) 5 V (d) 2 V
- **3.** Two identical Zener diodes are placed back to back in series and are connected to a variable DC power supply. The best representation of the



where *V* is measured in volts and *I* is measured in amperes.

The current *I* in the circuit is

(a) 10.0 mA

(c) 6.2 mA

[CSIR-DEC 2014] (b) 9.3 Ma (d) 6.7 mA

**5.** Let  $I_0$  be the saturation current,  $\eta$  the ideality factor and  $v_F$  and  $v_R$  the forward and reverse potentials, respectively, for a diode. The ratio  $R_R/R_F$  of its reverse and forward resistances  $R_R$  and  $R_F$  respectively, varies as (In the following  $k_B$  is the Boltzmani constant, *T* is the absolute temperature and *q* is the charge).

(a) 
$$\frac{v_R}{v_F} \exp\left(\frac{qv_F}{\eta k_B T}\right)$$
 (b)  $\frac{v_F}{v_R} \exp\left(\frac{qv_F}{\eta k_B T}\right)$   
(c)  $\frac{v_R}{v_F} \exp\left(-\frac{qv_F}{\eta k_B T}\right)$  (d)  $\frac{v_F}{v_R} \exp\left(-\frac{qv_F}{\eta k_B T}\right)$ 

**6.** A Zener diode with an operating voltage of 10 V at 25°C has a positive temperature co-efficient of 0.07% per °C of the operating voltage. The operating voltage of this Zener diode at 125°C is

(a) 12.0 V (b) 11.7 V

(c) 10.7 V (d) 9.3 V

7. In the circuit below,  $D_1$  and  $D_2$  are two silicon diodes with the same characteristics. If the forward voltage drop of a silicon diode is 0.7 V, then the value of the current  $I_1 + I_D$ , is



(c) 13.95 mA



8. A sinusoidal voltage having a peak value of  $V_P$  is an input to the following circuit, in which the DC voltage is  $V_b$ .

$$V_p$$
  $t$  Input  $D \neq 0$  Output

Assuming an ideal diode, which of the following best describes the output waveform?





[CSIR-DEC 2018]

**9.** The forward diode current is given by  $I = \kappa T^{\alpha} e^{-E_k/k_p T} (\exp(eV/k_B T) - 1)$ , where  $E_g$  is the band gap of the semiconductor, V is the voltage drop across the diode, T is the temperature of the diode operating near room temperature and,  $\alpha$  and  $\kappa$  are constants. A diode is used as a thermal sensor in the circuit shown below.



If V is measured using an ideal voltmeter to estimate T, the variation of the voltage V as a function of T is best approximated by (in the following a and b are constants)

(a)  $aT^2 + b$  (b) aT + b

(c)  $aT^3 + b$  (d)  $aT + bT^2$ 

**10.** In the circuit below, *D* is an ideal diode, the source voltage  $V_S = V_0 \sin \omega t$  is a unit amplitude sine wave and  $R_S = R_L$ .



The average output voltage  $V_L$ , across the load resistor  $R_L$  is

(a) 
$$\frac{1}{2\pi}V_0$$
  
(c)  $3V_0$ 

(d)  $V_0$ 

(b)  $\frac{3}{2\pi}V_0$ 

**11.** A high impedance load network is connected in the circuit as shown below



The forward voltage drop for silicon diode is 0.7 V and the Zener voltage is 9.10 V. If the input voltage ( $V_{in}$ ) is sine wave with an amplitude of 15 V (as shown in the figure above), which of the following waveform qualitatively describes the output voltage ( $V_{out}$ ) across the load? [CSIR-JUNE 2022]



connected to the centre tap of the secondary. Which one of the following plots represents the voltage across the resistor R as a function of time? [GATE 2012]



- 6. Consider the circuit given in the figure. Let the forward voltage drop across each diode be 0.7 V. The current *I* (in *mA* ) through the resistor is [GATE 2020]
- **7.** Choose the most appropriate matching of the items in Column 1 with those in Column 2.

[GATE 2023]

Column 2
P. Voltage regulation
Q. Radio frequency and microwave devices
R. Optoelectronic detection
S. Oscillator

(b) (i) - R; (ii) - Q; (iii) - P; (iv) - S

- (c) (i) R; (ii) S; (iii) P; (iv) Q
- (d) (i) P; (ii) Q; (iii) R; (iv) S
- **8.** The symbols C, D,  $V_{in}$  and  $V_0$  shown in the figure denote capacitor, ideal diode, input voltage and output voltage, respectively.



Which one of the following output waveforms  $(V_0)$  is correct for the given input waveform



#### JEST PYQ

**1.** Consider the circuit shown in the figure where  $R_1 = 2.07 \text{k}\Omega$  and  $R_2 = 1.93 \text{k}\Omega$  current source *I* delivers 10 mA current. The potential across the diode *D* is 0.7 V. What is the potential at *A* ?

[JEST 2017]



(a) 10.35 V

- (b) 9.65 V
- (c) 19.30 V (d) 4.83 V
- **2.** In the following silicon diode circuit ( $V_B = 0.7$  V), determine the output waveform ( $V_{out}$ ) for the given input wave. [JEST 2017]



- (c) 47.73 (d) 57.73
- **4.** The circuit given below is fed by a sinusoidal voltage  $V_{in} = V_0 \sin \omega t$ . Assume that the cut-in voltage of the diode is 0.7 volts and  $V_1$  is a positive dc voltage smaller than  $V_0$ . Which one of the following statements is true about  $V_{out}$ ?





(a) Positive part of  $V_{out}$  is restricted to a maximum voltage of  $0.7 + \frac{R_2}{R_1 + R_2}V_1$ 

(b) Negative part of  $V_{out}$  is restricted to a maximum voltage of  $0.7 + \frac{R_2}{R_1 + R_2} V_1$ 

(c) Positive part of  $V_{out}$  is restricted to a maximum voltage of  $0.7 + \frac{R_1}{R_1 + R_2}V_1$ 

(d) Negative part of  $V_{out}$  is restricted to a maximum voltage of  $0.7 + \frac{R_1}{R_1 + R_2}V_1$ 

- **5.** In an open circuited p n junction diode, the barrier voltage at the junction is generated due to [JEST 2021]
  - (a) Minority carriers in the p and n sides
  - (b) Majority carriers in the p and n sides

(c) Immobile negative charge in the *p*-side and positive charge in the *n*-side

(d) Immobile positive charge in the *p*-side and negative charge in the *n*-side

**6.** The circuit given in the figure below is composed of ideal diodes and resistances *R*. The input waveform is shown on the left.





(b)



-5V

7. What is the output waveform of the circuit for the given input signal? Assume that the zener diodes are identical, amplitude of the input voltage  $V_{in}$  is twice the zener breakdown voltage, and  $R_L = 10R$ .

[JEST 2024]



Drawing power from a 12 V car battery, a 9 V 4. stabilized DC voltage is required to power a car stereo system, attached to the terminals A and *B*, as shown in the figure.

If a Zener diode with ratings,  $V_z = 9 V$  and  $P_{max} = 0.27$  W, is connected as shown in the figure, for the above purpose, the minimum series resistance  $R_S$  must be [TIFR 2019]



- 5. The signal shown on the left side of the figure
- below is fed into the circuit shown on the right side.

$$\mathbf{v}_{m}$$
  
 $\mathbf{v}_{in}$   
 $\mathbf{v}$ 

If the signal has time period  $\tau_S$  and the circuit has a natural frequency  $\tau_{RC}$ , then, in the case when  $\tau_S \ll \tau_{RC}$ , the steady-state output will resemble [TIFR 2019]







R R

o B



## **ANALOG ELECTRONICS: Bipolar Junction Transistor**

#### ✤ CSIR-NET PYQ

1. The transistor in the given circuit has  $h_{fc} = 35\Omega$ and  $h_{ie} = 1000\Omega$ . If the load resistance  $R_L = 1000\Omega$ , the voltage and current gain are, respectively. **[CSIR-JUNE 2012]** 



2. A silicon transistor with built-in voltage 0.7 V is used in the circuit shown, with  $V_{BB} = 9.7 \text{ V}$ ,  $R_B = 300 \text{k}\Omega$ ,  $V_{CC} = 12 \text{ V}$  and  $R_C = 2\text{k}\Omega$ . Which of the following figures correctly represents the load line and the quiescent *Q* point?



**3.** A large MOS transistor consists of N individual transistors connected in parallel. If the only form of noise in each transistor is 1/f noise, then the equivalent voltage noise spectral density for the MOS transistor is

#### [CSIR-DEC 2014]

- (a) 1/N times that of a single transistor
- (b)  $1/N^2$  times that of a single transistor
- (c) *N* times that of a single transistor

(d)  $N^2$  times that of a single transistor

4. Consider the circuits shown in Figures (a) and (b) below.



If the transistors in Figures (a) and (b) have current gain ( $\beta_{\rm tik}$ ) of 100 and 10 respectively, then they operate in the

#### [CSIR-JUNE 2015]

(a) active region and saturation region respectively

(b) saturation region and active region respectively

- (c) saturation region in both cases
- (d) active region in both cases
- 5. In the circuit below the voltages  $V_{BB}$  and  $V_{CC}$  are kept fixed, the voltage measured at *B* is a constant, but that measured at *A* fluctuates between a few  $\mu V$  to a few mV.



From these measurements it may be inferred that the **[CSIR-DEC 2017]** (a) base is open internally

- (b) emitter is open internally
- (c) collector resistor is open
- (d) base resistor is open
- 6. In the following circuit, the value of the common-emitter forward current amplification factor  $\beta$  for the transistor is 100 and  $V_{BE}$  is



Input •

The value of the base current  $I_B$  is

[CSIR-DEC 2019]

(a)  $20\mu A$  (b)  $40\mu A$ 

(c) 10µA (d) 100µA

9. The figure below shows a circuit with two transistors,  $Q_1$  and  $Q_2$ , having current gains  $\beta_1$  and  $\beta_2$  respectively.



The collector voltage V <sub>C</sub> will be closest to				
(a)0.9 V	<b>[CSIR-JUNE 2022]</b> (b)2.2 V			
(c)2.9 V	(d)4.2 V			

10. An amplifier with a voltage gain of 40 dB without feedback is used in an electronic circuit. A negative feedback with a fraction 1/40 is connected to the input of this amplifier. The net gain of the amplifier in the circuit is closest to

(a)40 dB	<b>[CSIR-JUNE 2022</b> ] (b)37 dB		
(c)29 dB	(d)20 Db		

**11.** An LED is required to glow brightly when the temperature sensed by a Platinum resistance thermometer exceeds a certain value. In the circuit shown below, the resistance of the Pt thermometer (in ohms) varies as

 $R_{Pt}(T) = 100 + 0.4 T$ where *T* is temperature in degree Celsius. The transistor turns on when  $V_{BE} > 0.7$  V and it has a very high current gain. The temperature at which the LED would start glowing is closest to [CSIR DEC 2024]

	•+10V			(a) 40mV	(b) 60Mv	
	5kΩ ₹	$1k\Omega$		(c) 80mV	(d) 100mV	
		<b>4.</b> Calculate the collector voltage $(v_c)$ of the transistor circuit is shown in the figure. [Given: $\alpha = 0.96$ , $I_{CB0} = 20\mu A$ , $V_{BE} = 0.3 \text{ V}$ , $R_B = 100 \text{ k}\Omega$ , $V_{CC} = +10 \text{ V}$ and $R_C = 2.2 \text{ k}\Omega$ ]				
			V	[GATE 2004]		
	(a)850°C	(b)400°C				
	(c)500°C	(d)700°C				
*	GATE PYQ			(a) 3.78 V	(b) 3.82 V	
1.	In an $n - p - n$ transistor consists of	; the leakage current [GATE 2001]		(c) 4.72 V	(d) 9.7 V	
	emitter		5.	A power amplifier gives 150 W output for an input of 1.5 W. The gain, in dB, is [GATE 2007]		
	(b) electrons moving from base	n the collector to the		(a) 10 (c) 54	(b) 20 (d) 100	
	(c) electrons moving from the collector to the emitter			<b>6.</b> In a typical <i>npn</i> transistor the doping		
	(d) electrons moving from the base to the collector			regions are $C_E$ , $C_B$ and $C$ satisfy the relation (a) $C_E > C_C > C_B$	$_{C}$ respectively. These [GATE 2007] (b) C $_{E} > C_{B} > C_{C}$	
2.	A bipolar junction transis forward biased and either	tor with one junction r the collector or		(c) $C_{C} > C_{B} > C_{E}$	$(d) C_E = C_C > C_B$	
	emitter open, operates in (a) cut-offregion	(b) saturation region	7.	A common emitter trans operated under a fixed b	sistor amplifier circuit is bias. In this circuit, the	
	(c) pinch-offregion	(d) active region		operating point (a) remains fixed with a	[GATE 2008] n increase in	
3.	Figure shows a common e	emitter amplifier with		temperature		
	$\beta = 100$ . What is the maximum peak to peak input signal ( $v_s$ ) for which is distortion-free output may be obtained? [GATE 2004]			(b) moves towards cut-off region with an increase in temperature		
[Assume $V_{BE} = 0$ and $r_e = 20\Omega$ ]			(c) moves towards the saturation region with a			
$500 \text{ k}\Omega$			decrease in temperature	2		
			(d) moves towards the saturation region with an increase in temperature			
8. An amplifier of gain 1000 is made into a feedback amplifier by feeding 9.9% of its output voltage in series with the input opposing. If  $f_L = 20$  Hz and  $f_H = 200$ kHz for the amplifier without feedback, then due to the feedback

[GATE 2009]

- (a) the gain decreases by 10 times
- (b) the output resistance increases by 10 times
- (c) the  $f_H$  increases by 100 times
- (d) the input resistance decreases by 100 times
- **9.** Consider the following circuit in which the current gain  $\beta_{dc}$  lof the transistor is 100



Which one of the following correctly represent<br/>the load line (collector current  $I_C$  with respect<br/>to collector emitter voltage  $V_{CE}$ ) and Q-point of<br/>this circuit?[GATE 2012]



**10.** The current gain of the transistor in the following circuit is  $\beta_{dc} = 100$ . The value of collector current I<sub>C</sub> is [GATE 2014]



**11.** In the simple current source shown in the figure,  $Q_1$  and  $Q_2$  are identical transistors with current gain  $\beta = 100$  and  $V_{BE} = 0.7$  V



**12.** For the transistor shown in the figure, assume  $V_{BE} = 0.7$  V and  $\beta_{dc} = 100$ . If  $V_{in} = 5$  V,  $V_{out}$  (in Volts) is\_\_\_\_\_ (Give your answer upto one decimal place) [GATE 2016]



**13.** For the transistor amplifier circuit shown below with  $R_1 = 10k\Omega$ ,  $R_2 = 10k\Omega$ ,  $R_3 = 1k\Omega$  and  $\beta =$  99. Neglecting the emitter diode resistance, the input impedance of the amplifier looking into the base for small ac signal is k $\Omega$ . (up to two decimal places)

[GATE 2017]

14. For a bipolar junction transistor, which of the following statements are true? [GATE 2022](a) Doping concentration of emitter region is more than that in collector and base region



(b) Only electrons participate in current conduction

(c) The current gain  $\beta$  depends on temperature

(d) Collector current is less than the emitter current

- 15. For a transistor amplifier, the frequency response is such that the mid band voltage gain is 200. The cutoff frequencies are 20 Hz and 20kHz. What is the ratio (rounded off to two decimal places) of the voltage gain at 10 Hz to that at 100kHz?
- **16.** A typical biasing of a silicon transistor is shown in figure.



The value of common-emitter current gain  $\beta$  for the transistor is 100. Ignore reverse saturation current. The output voltage  $V_0$  (in V) is (in integer).

#### [GATE 2024]

**17.** In the transistor circuit shown in the figure,  $V_{BE} = 0.7$  V and  $\beta_{DC} = 400$ . The value of the base current in  $\mu$ A (rounded off to one decimal place) is



#### JEST PYQ

 A transistor in common base configuration has ratio of collector current to emitter current β and ratio of Collector to base current α. Which of the following is true? [JEST 2016]

(a)
$$\beta = \frac{\alpha}{(\alpha + 1)}$$
 (b) $\beta = \frac{(\alpha + 1)}{\alpha}$ 

$$(c)\beta = \frac{\alpha}{(\alpha - 1)}$$
 (d)  $\beta = \frac{(\alpha - 1)}{\alpha}$ 

2. What is the DC base current (approximated to nearest integer value in  $\mu$ A) for the following n - p - n silicon transistor circuit, given  $R_1 = 75\Omega$ ,  $R_2 = 4.0 k\Omega$ ,  $R_3 = 2.1 k\Omega$ ,  $R_4 = 2.6 k\Omega$ ,  $R_5 = 6.0 k\Omega$ ,  $R_6 = 6.8 k\Omega$ ,  $C_1 = 1 \mu F$ ,  $C_2 = 2 \mu F$ ,  $V_C = 15V$  and  $\beta_{dc} = 75$ ? [JEST 2017]



**3.** Consider the transistor circuit shown in the figure. Assume  $V_{BEO} = 0.7 \text{ V}$ ,  $V_{BB} = 6 \text{ V}$ 



And the leakage current is negligible. What is the required value of  $R_B$  in kilo-ohms if the base current is to be  $4\mu A$ ?

[JEST 2018]

**4.** Calculate the collector current and determine whether or not the transistor in figure shown below is in saturation. Assume  $V_{CE}(\text{ sat }) = 0.2 \text{ V}$ 



6. The circuit shown below represents a typical (c) 17 mW (d) 67 Mw voltage-divider bias circuit for a transistor. Assume that resistance values and voltage values are typical for using the transistor as an tolerance of  $\pm 5\%$ . amplifier. Assuming a diode drop of 0.7 V, which of the [TIFR 2020] following is the lowest possible value of the collector voltage? [TIFR 2014] o+Vcc 0+10 V 150 kΩ R<sub>1</sub> 330 kΩ ≩ 100 kΩ ≥ 51 kΩ  $R_2$ (a) 3.1 V (b) 4.1 V Which of the following changes in the circuit (d) 5.2 V (c) 4.7 V would result in an increase in the collector voltage  $V_C$ ? 4. In the transistor circuit shown on the right, (a) R<sub>2</sub> is decreased slightly assume that the voltage drop between the base and the emitter is 0.5 V. (b)  $R_2$  is increased slightly What will be the ratio of the resistances  $R_2/R_1$ , in order to make this circuit function as a source (c) R<sub>c</sub> is decreased slightly of constant current, l = 1mA? [TIFR 2016] (d)  $R_c$  is increased slightly  $R_2$ 7.5 V 2 kΩ

2. The circuit depicted on the right has been made with a silicon n-p-n transistor.

Assuming that there will be a 0.7 V drop across a forward-biased silicon p-n junction, the power dissipated across the transistor will be, approximately,

[TIFR 2013]

(b) 94 mW



- (a) 53 mW
- **3.** All resistors in the circuit on the right have a

- (a) 4.5 (b) 3.0
- (c) 2.5 (d) 2.0
- 5. Which digital logic gate is mimicked by the following silicon diode and silicon transistor circuit? [TIFR 2017]



			🔹 🚸 🔺	nsw	ver Key				
			CS	SIR-I	NET				
1.	а	2.	с	3.	а	4.	b	5.	d
6.	d	7.	d	8.	а	9.	b	10.	С
11.	. d								
				GAT	Έ				
1.	С	2.	с	3.	d	4.	а	5.	
6.	а	7.	а	8.	С	9.	а	10.	
11.	. 5.6to5.9	12.	5.7	13	. 5	14.	acd	15.	
16	. 12	17.	18.6µA						
				JES	Т				
1.	а	2.	а	3.	1325Κω	4.	а	5.	b
6.	0950	7.	С						
				TIF	R				
1.		2.	b	3.	b	4.	d	5.	
6.	а								

GATE Q.15 : 2.20 to 2.36

TIFR Q. 5 : AND or (A.B)

# D PHYSICS

## ANALOG ELECTRONICS: MOSFET, JFET





## ANALOG ELECTRONICS: Semiconductor

#### ✤ CSIR-NET PYQ

- Light of wavelength 660 nm and power of 1 mW is incident on a semiconductor photodiode with an absorbing layer of thickness of (ln 4)μm.
   (A) If the absorption coefficient at this wavelength is 10<sup>4</sup> cm<sup>-1</sup> and if 1% power is lost on reflection at the surface, the power absorbed will be [CSIR JUNE 2011]

   (a) 750μW
   (b) 675μW
  - (c)  $250\mu$ W (d)  $225\mu$ W

(B)The generated photo-current for a quantum efficiency of unity will be

(a) 360µA

(b) 400µA

(c) 133µA

(d) 120µA

**2.** A junction is made between a metal of work function  $W_M$ , and a doped semiconductor of work function  $W_S$  with  $W_M > W_S$ . If the electric field at the interface has to be increased by a factor of 3, then the dopant concentration in the semiconductor would have to be

[CSIR-DEC 201<mark>4</mark>]

(a) increased by a factor of 9

(b) decreased by a factor of 3

(c) increased by a factor of 3

(d) decreased by a factor of  $\sqrt{3}$ 

**3.** If the reverse bias voltage of a silicon varactor is increased by a factor of 2 , the corresponding transition capacitance

[CSIR-DEC 2015]

- (a) increases by a factor of  $\sqrt{2}$
- (b) increases by a factor of 2
- (c) decreases by a factor of  $\sqrt{2}$
- (d) decreases by a factor of 2
- **4.** The I V characteristics of a device is  $I = I_s \left[ \exp \left( \frac{aV}{T} \right) 1 \right]$ , where *T* is the temperature and *a* and  $I_s$  are constants independent of *T* and

*V*. Which one of the following plots is correct for a fixed applied voltage *V* ?

#### [CSIR-DEC 2016]







- 5. Optical excitation of intrinsic germanium creates an average density of  $10^{12}$  conduction electrons per cm<sup>3</sup> in the material at liquid nitrogen temperature. At this temperature, the electron and hole mobilities are equal,  $\mu =$  $0.5 \times 10^4$  m<sup>2</sup> V<sup>-1</sup> s<sup>-1</sup>. The germanium dielectric constant is 20. If 100 Volts is applied across 1 cm cube of crystal under these condition, about how much current, in mA, is observed? [Charge of electron =  $1.6 \times 10^{-19}$ C] [JEST 2022]
- 6. A silicon crystal sample has 50 billion silicon atoms and 5 million free electrons. The silicon crystal is additionally doped with 5 million pentavalent atoms. Assume that the ambient thermal energy is much smaller than the bandgap of silicon. How many free electrons and holes are there inside the silicon crystal? [JEST 2023]

(a) Number of electrons is 30 million and number of holes is zero.

(b) Number of electrons is 10 million and number of holes is zero.

(c) Number of electrons is 10 million and number of holes is 5 million.

(d) Number of electrons is 5 million and number of holes is 5 million.

#### ✤ GATE PYQ

 A piece of semiconducting material is introduced into a circuit. If the temperature of the material is raised, the circuit current will

	[GATE 2001]
(a) increase	(b) remain the same

- (c) decrease (d) cease to flow
- Which one of the following is TRUE for a semiconductor *p* junction with no external bias? [GATE 2003]

(a) The total charge in the junction is not conserved

(b) The *p* side of the junction is positively charged

(c) The *p* side of the junction is negative charged

(d) No charge develops anywhere in the junction

**3.** The temperature dependence of the electrical conductivity  $\sigma$  of two intrinsic semiconductors A and B is shown in the figure. If  $E_A$  and  $E_B$  are the band gaps of A and B respectively, which one of the following is TRUE?

[GATE 2004]



- (a)  $E_A > E_B$
- (b)  $E_A < E_B$
- (c)  $E_A = E_B$
- (d)  $E_A$  and  $E_B$  both depend on temperature

4. An intrinsic semiconductor with mass of a hole  $m_h$  and mass of an electron  $m_e$  is at a finite temperature T. If the top of the valence band energy is  $E_v$  and the bottom of the conduction band energy is  $E_c$ , the Fermi energy of the semiconductor is [GATE 2008]

(a)
$$E_F = \left(\frac{E_y + E_c}{2}\right) - \frac{3}{4}k_BT\ln\left(\frac{m_h}{m_c}\right)$$
  
(b) $E_r = \left(\frac{k_BT}{2}\right) + \frac{3}{4}(E_r + E_r)\ln\left(\frac{m_h}{m_c}\right)$ 

$$(0)E_F = \left(\frac{1}{2}\right) + \frac{1}{4}(E_v + E_c) \prod \left(\frac{1}{m_c}\right)$$

$$(c)E_F = \left(\frac{E_v + E_c}{2}\right) + \frac{3}{4}k_BT\ln\left(\frac{m_h}{m_c}\right)$$

$$(\mathbf{d})E_F = \left(\frac{k_BT}{2}\right) - \frac{3}{4}(E_v + E_c)\ln\left(\frac{m_h}{m_c}\right)$$

5. A phosphorous doped silicon semiconductor (doping density: 10<sup>17</sup>/cm<sup>3</sup>) is heated from 100°C to 200°C. which one of the following statements is correct? [GATE 2013]
(a) position of fermi level moves towards conduction band

(b) position of dopant level moves towards conduction band

(c) position of fermi level moves towards middle of energy gap

(d) position of dopant level moves towards middle of energy gap

6. The number density of electron in the conduction band of a semiconductor at a given temperature is  $2 \times 10^{19}$  m<sup>-3</sup>. Upon lightly doping this semiconductor with donor impurities, the number density of conduction electrons at the same temperature becomes  $4 \times 10^{20}$  m<sup>-3</sup>. The ratio of majority to minority charge carrier concentration is\_\_\_\_\_.

[GATE 2016]

7. A junction is formed between a metal on the left and an *n*-type semiconductor on the right. Before forming the junction, the Fermi level  $E_F$ of the metal lies below that of the semiconductor. Then which of the following schematics are correct for the bands and the I - V characteristics of the junction?





(b)	$E_F$	$E_F$
	Metal	n-type semiconductor Valence Band



			*	Ans	swer K	ley			
				CSIF	R-NET				
1.	c/c	2.	а	3.	С	4.	d	5.	0.333
6.	b								
				G	ATE				
1.	а	2.	С	3.	а	4.	С	5.	С
6.	400	7.	ac/ad						
				Т	IFR				
1.									

#### ✤ TIFR PYQ

- The sign of the majority charge carriers in a doped silicon crystal is to be determined experimentally. In addition to a voltage supply, the combination of instruments needed to perform the experiment is [TIFR 2011]

   (a) Thermometer, Voltmeter and Ammeter
  - (b) Pickup Coil, Voltmeter and Ammeter
  - (c) Magnet, Voltmeter and Ammeter
  - (d) Heater, Magnet and Thermometer

## ANALOG ELECTRONICS: Transient Circuit

#### ✤ CSIR-NET PYQ

An inductor *L*, a capacitor *C* and a resistor *R* are connected in series to an *AC* source, *V* = *V*<sub>0</sub>sin ω*t*. If the net current is found to depend only on *R*, then [CSIR-JUNE 2020]

 (a) *C* = 0
 (b) *L* = 0

(c)
$$\omega = 1/\sqrt{LC}$$
 (d)  $\omega = \sqrt{\frac{1}{LC} - \frac{R^2}{4L^2}}$ 

**2.** A 10 V battery is connected in series to a resistor *R* and a capacitor *C*, as shown the figure.



The initial charge on the capacitor is zero. The switch is turned on and the capacitor is allowed to charge to its full capacity. The total work done by the battery in this process is

(a) 10<sup>-3</sup> J

(b)  $2 \times 10^{-3}$  J

[CSIR-JUNE 2020]

(d)  $47 \times 10^{-2}$ 

- (c)  $5 \times 10^{-4}$  J
- **3.** In the LCR circuit shown below, the resistance  $R = 0.05\Omega$ , the inductance L = 1H and the capacitance C = 0.04 F.

If the input  $v_{in}$  is a square wave of angular frequency 1rad/s the output  $v_{out}$  is best approximated by a

[CSIR-JUNE 2021]

- (a) square wave of angular frequency 1rad/s
- (b) sine wave of angular frequency 1rad/s
- (c) square wave of angular frequency 5rad/s
- (d) sine wave of angular frequency 5rad/s
- **4.** An ideal inductor *L* is connected in series to a  $150\Omega$  resistor as shown in the circuit (inset). When the circuit is driven by a battery *B*<sub>1</sub>, the

voltage across the resistor as a function of time, as measured by an oscilloscope, is shown in the plot.



Based on this observation, the estimated valueof L is closest to[CSIR DEC 2024](a)50 mH(b)300 mH

(c)450 mH

(d)150 mH

#### ✤ GATE PYQ

- **1.** For high frequencies  $(\omega \rightarrow \infty)$  the input impedance is [GATE 2003] (a) 0 (b) R
  - (c)  $R/(1 + \omega RC)$  (d)  $\infty$
- **2.** For low frequencies  $(\omega \to \infty)$  the input impedance is [GATE 2003] (a)  $V_0 = (1/RC) \int V_1 dt$

(b) The voltages at the inverting and noninverting terminals of the op-amp are nearly

(c) The voltage at the non-inverting terminal of the op-amp and the current in the resistor attached to it are  $\pi/2$  out of phase

- (d) The current in the two resistors are in phase
- **3.** The figure shows a constant current source charging a capacitor that is initially unchanged [GATE 2010]







The capacitor is initially uncharged. At time t = 0, the switch *S* is closed. The voltage across the capacitor as a function of time ' *t* ' for t > 0 is given by [JEST 2012] (a)  $(V_0/2)(1 - \exp(-t/2\text{Rc}))$ 

(b)  $(V_0/3)(1 - \exp(-t/3Rc))$ 

(c) 
$$(V_0/3)(1 - \exp(-3t/2Rc))$$

(d)  $(V_0/2)(1 - \exp(-2t/3Rc))$ 

**2.** Find the resonance frequency (rad/sec) of the circle shown in the figure below



**3.** Consider the following circuit in steady state condition. Calculate the amount of charge stored in  $1\mu$ F and  $2\mu$ F capacitors respectively. [JEST 2017]



**4.** In the circuit shown below, the capacitor is initially uncharged. Immediately after the



Key K is closed, the reading in the ammeter is 27 mA. What will the reading (in mA ) be a long time later ? [JEST 2018]

5. What is the charge stored on each capacitor C<sub>1</sub> and C<sub>2</sub> in the circuit shown in the given figure?[JEST 2020]



6. A capacitor with capacitance C is connected in series with a resistor of resistance R and an ideal DC source with voltage  $V_S$ . At one instant during the charging of the capacitor if the resistor is replaced by a wire of zero resistance, which of the following statements is true? (a)The voltage across the capacitor will increase slowly.

(b)None of the others is true.

(c) The capacitor immediately attains the source voltage  $V_S$ .

(d)The voltage across the capacitor will drop immediately to zero.

#### ✤ TIFR PYQ

 Two parallel plates of metal sandwich a dielectric pad of thickness *d*, forming an ideal capacitor of capacitance *C*. The dielectric pad is elastic, having a spring constant *k*. If an ideal battery of voltage *V* across its terminals is connected to the two plates of this capacitor, the fractional change  $\delta d/d \ll 1$  in the gap between the plates is [TIFR 2009]

(a) zero

(b) 
$$+\frac{\frac{1}{2}CV^2}{kd^2}$$

(c) 
$$-\frac{\frac{1}{2}CV^2}{kd^2 + CV^2}$$
 (d)  $-\frac{\frac{1}{2}CV^2}{kd^2 - CV^2}$ 

**2.** Two LCR circuits (A) and (B) are shown below where  $C_c \ll C$ . At time t = 0, a charge Q is put on the capacitor C.

Which of the following statements is correct?
[TIFR 2014]

- (a) The charge Q will decay faster in (A)
- (b) The charge *Q* will decay faster in (B)

(c) The charge *Q* will decay at the same rate in (A) and (B)

(d) The relative decay rates cannot be predicted without knowing the exact values of L, C, R and  $C_c$ 

**3.** The circuit diagram on the right shows a block A representing a cubic structure comprising 12 identical resistances of  $120\Omega$  each, whose body diagonal vertices are connected to the rest of the circuit with an inductor L = 10mH, a resistor R =  $100\Omega$ , and a capacitor C =  $1\mu$ F. Now, the switch *S* is turned on at t = 0. The



earliest time at which the current reaches asteady value  $I_0$  is[TIFR 2022](a) infinite(b)  $100\mu$ s

- (c) 200µs (d) zero
- It is required to design a circuit with an impedance Z(ω) such that

 $Z(\omega) = ik(\omega - \omega_0)$ for a range of frequencies  $\omega$  such that  $|\omega - \omega_0|/\omega_0 \ll 1$ where *k* and  $\omega_0$  are constant real numbers.



## **ANALOG ELECTRONICS: ADC & DAC**



- analog-to-digital (A/D) converter operating in the voltage range 0 to  $V_0$ . The output of the
- (c) 100 (d) 010

Coding

network

Read

Gates+ Flip – Flops • 1<sup>st</sup> bit

• 2<sup>st</sup> bit

[GATE 2006]

[GATE 2008]

[GATE 2013]

[GATE 2019]

(b) 101

(a) 011

<b>*</b> 1.	JEST P conver the conver (a) 0.2	YQ rter is nverte rter is 24 V	1 V. T er can	'he s reco	smalles ord usi (	st vo ing a b) 0.	ltage s 12 -bi <b>[JES</b> 24Mv	tep t t T 20	hat 15]		
	(c) 0.2	24μV			(	d) 0.	24Nv				
2.	<ul> <li>A 16-bit analog to digital converter works in the range 0 - 1 Volt. The least count of the converter is [JEST 2020]</li> </ul>										
	(a) 0.3	80mV			(	b) 1	5.26m	V			
	(c) 5.44 <i>nV</i> (d) 15.26 <i>µ</i> V										
3.	A 12-	bit an	alog-t	o-di	gital co	onve	rter ha	as an			
	volta	ung n te ster	ange ( 5 (in r	nV i	$10 \pm v.$	nne vo si	smane onifica	est int di	ioite`	`	
	that o	one ca	n reco	ord u	sing th	nis co	onvert	er is	igno,	)	
							[JES	T 20	22]		
			*	Ar	sw <u>er</u>	Key					
				CSI	R-NET						
1	. с	2.	a	3.	а	4.	а	5.	С		
				G	ATE						
1	. с	2.	а	3.	а	4.	С				
		0	,	J	EST						
1	. b	2.	d	3.	0.24						

## **D**PHYSICS

## ANALOG ELECTRONICS: Experimental Instruments Based Problems

#### CSIR-NET PYQ

 The pins 0,1,2, and 3 of part A of a microcontroller are connected with resistors to drive an LED at various intensities as shown in the figure.



For  $V_{co} = 4.2$  V and a voltage drop of 1.2 Vacross the LED, the range (maximum current)and resolution (Step size) of the drive currentare, respectively,(a) 4.0 mA and 1.0 mA

- (b) 15.0 mA and 1.0 mA
- (c) 7.5 mA and 0.5 mA
- (d) 4.0 mA and 0.5 mA
- **2.** The output characteristics of a solar panel at a certain level of irradiance is shown in the figure below.



If the solar cell is to power a load of 5Ω, the power drawn by the load is: **[CSIR-DEC 2012]** (a) 97 W (b) 73 W

(c) 50 W (d) 45 W

**3.** The input to a lock-in amplifier has the form  $V_i(t) = V_i \sin(\omega t + \theta_i)$  where  $V_i, \omega, \theta_i$  are the amplitude, frequency and phase of the input

signal respectively. This signal is multiplied by a reference signal of the same frequency  $\omega$ , amplitude V<sub>r</sub> and phase  $\theta_f$ . If the multiplied signal is fed to a low pass filter of cut-off frequency  $\omega$ , then the final output signal is **[CSIR-JUNE 2013]** 

(a) 
$$\frac{1}{2} V_i V_r \cos(\theta_i - \theta_r)$$

(b)
$$V_i V_r \left[ \cos \left( 0_i - 0_r \right) - \cos \left( \frac{1}{2} \omega t + \theta_i + \theta_r \right) \right]$$

(c)  $V_i V_r \sin(\theta_i - \theta_r)$ 

$$(d)V_{i}V_{r}\left[\cos\left(\theta_{i}-\theta_{r}\right)+\cos\left(\frac{1}{2}\omega t+\theta_{i}+\theta_{r}\right)\right]$$

- 4. If the reverse bias voltage of a silicon varactor is increased by a factor of 2, the corresponding transition capacitance [CSIR-DEC 2015]
  (a) increases by a factor of √2
  - (b) increases by a factor of 2
  - (c) decreases by a factor of  $\sqrt{2}$
  - (d) decreases by a factor of 2
- A receiver operating at 27°c has an input resistance of 100Ω. The input thermal noise voltage for this receiver with a bandwidth of 100kHz is closest to [CSIR-JUNE 2022]

(a)0.4nV	(b)0.6pV
(c)40mV	(d)0.4µV

6. A circuit needs to be designed to measure the resistance *R* of a cylinder *PQ* to the best possible accuracy, using an ammeter *A*, a voltmeter *V*, a battery *E* and a current source  $I_S$  (all assumed to be ideal). The value of *R* is known to be approximately  $10\Omega$ , and the resistance *W* of each of the connecting wires is close to  $10\Omega$ . If the current from the current source and voltage from the battery are known exactly, which of the following circuits provides the most accurate measurement of *R* ?



7. A piezoresistive pressure sensor utilizes change in electrical resistance ( $\Delta R$ ) with change in pressure ( $\Delta P$ ) as  $\Delta R = -R_0 \log_{10} \left(\frac{\Delta P}{P_0}\right)$ , where  $R_0 = 500\Omega$  and  $P_0 = 1000$ mbar. A current of  $2\mu A$  is passed through the sensor and the resultant voltage drop is measured using an analog-to-digital (ADC) converter having a range 0 to 1 V. If a pressure change of 1 mbar is to be measured, amongst the given options, the minimum number of bits needed for the ADC is **[CSIR JUNE 2024]** 

(a)12		
(a)12		

(d)10

(b)14

#### ✤ TIFR PYQ

(c)8

1. Consider a very, very thin wire of uniformly circular cross section. The diameter of the wire is of the order of microns. The correct equipment required to measure the precise value of resistivity of this wire is

#### [TIFR 2009]

(a) ammeter, voltmeter, scale, slide calipers

(b) ammeter, magnet, screw gauge, thermometer

(c) voltmeter, magnet, screw gauge, scale

(d) ammeter, voltmeter, scale, monochromatic laser source

2. In a scanning tunnelling microscope, a fine Platinum needle is held close to a metallic surface in vacuum and electrons are allowed to tunnel across the tiny gap  $\delta$  between the surface and the needle. The tunnelling current I is related to the gap  $\delta$ , through positive

constants a and b, as[TIFR 2012](a)  $I = a - b\delta$ (b)  $I = a + b\delta$ 

(c)  $\log I = a - b\delta$  (d)  $\log I = a + b\delta$ 

 A photomultiplier tube is used to detect identical light pulses each of which consists of a fixed number of photons. The photoelectric efficiency is 10%, i.e. a photon has 10% probability of causing the emission of a detectable photoelectron. The photomultiplier gain is 10<sup>6</sup>.

The typical output current, as a function of time, is shown by the figure below for a few pulses, where  $I_{\text{max}}$  is 80 $\mu$ A. It follows that the number of photons in each pulse is (a)  $5 \times 10^6$  (b) 5

(c) 800 (d) 50

4. On passing electric current, a tungsten filament is emitting electrons by thermionic emission. In order to maintain the energy of the electron beam obtained from this source at a value approximately 100eV, which of the following methods will work in practice? [TIFR 2020]

(a) Float the filament at -100 Volts with a grounded aperture in front of it.

(b)Heat the filament so that the emitted electrons will have 100eV kinetic energy due to temperature.

(c)Apply a +100 Volts potential with respect to the filament potential to an aperture kept very close to the filament.

(d)Use an appropriate magnetic field to draw out the electron beam at the desired energy without applying any electric field.

**5.** A well-collimated constant-current electron beam of Gaussian energy distribution centered

at 10eV with FWHM of 2eV is detected using a metal cup connected to an ammeter, as shown in the figure below. The entire apparatus is kept in vacuum.



To measure the energy width of the electron beam, a grid is introduced with a voltage source  $V_{\text{stop}}$  connected to it, as shown in the figure. The current measured in the cup is plotted as a function of the value of  $V_{\text{stop}}$ . The graph of the current I vs  $V_{\text{stop}}$  would be



6. Two small loudspeakers A and B, separated by 15 cm, were pointed toward a small microphone M at a distance 1.5 m away from the centre of the line AB, in the perpendicular direction as shown in the sketch below.

A

В

O M

The following sound intensity pattern was observed as a function of the position of the microphone as it is moved parallel to AB.



The dips in the signal were repeated at the interval of 14.5 cm. The speed of sound in the experiment's background condition is 343 m/s. What can we conclude from this information? [TIFR 2024]

(a) The two loudspeakers are vibrating at frequency 23.65kHz and they are out of phase.

(b) The two loudspeakers are vibrating at frequency 23.65kHz and they are in phase.

(c) The two loudspeakers are vibrating at frequency 47.3kHz and they are in phase.

(d) The two loudspeakers are vibrating at frequency 47.3kHz and they are out of phase.

7. Consider a charge particle detection chamber as shown in the figure below. The chamber is made of a set of parallel plates separated by 20 mm distance and connected to the external resistance ( $R = 100\Omega$ ) as shown in the figure along with the high voltage power supply of 1kV.



V<sub>0</sub>=1 kV

The chamber is filled with Argon (Ar) gas (ionization energy 16eV). If a charged particle passes through the chamber and loses sufficient energy, it ionizes the Ar atoms and generates a small voltage pulse across the resistance R.

In an experiment, an alpha particle of energy 5.5MeV enters the chamber at a distance of 4 mm from the bottom plate, as shown, generating ion-electron pairs. If the effective capacitance of the chamber is 100pF, the measured voltage pulse shape would be best described as:

(a) No voltage pulse would be generated as both electrons and ions will neutralize the charge collected by the capacitor

(b) Two sharp voltage pulses of equal magnitude and opposite signs

(c) Two sharp voltage pulses of the same magnitude and sign

(d) A sharp voltage pulse followed by a very weak broad pulse

	<ul> <li>Answer Key</li> </ul>							
	CSIR-NET							
1.	С	2.	d	3. a	4. c	5. d		
6.	b	7.	d					
				TIFR				
1.		2.	С	3. a,b	4. a	5. a		
6.		7.	d					



## ANALOG ELECTRONICS: Wave Shaping

#### ✤ CSIR-NET PYQ

 The figure below shows a voltage regulator utilizing a Zener diode of breakdown voltage 5 V and a positive triangular wave input of amplitude 10 V.



For  $V_i > 5$  V, the Zener regulates the output voltage bychanneling the excess current through it self. Which of the following waveforms shows the current '*i*' passing through the Zener diode?



**2.** For the circuit and the input sinusoidal waveform shown in the figures below, which is the correct waveform at the output?



(The time scales in all the plots are the same).



**3.** Given the input voltage  $V_i$ , which of the following waveforms correctly represents the output voltage  $V_0$  in the circuit shown below?



**4.** A sinusoidal signal with a peak voltage  $V_p$  and average value zero, is an input to the following circuit.



Assuming ideal diodes, the peak value of the output voltage across the load resistor  $R_L$ , is [CSIR-JUNE 2018]

- (a)  $V_P$  (b)  $V_P/2$
- (c)  $2V_P$  (d)  $\sqrt{2}V_P$
- **5.** A sinusoidal signal is an input to the following circuit:



The forward voltage drop for silicon diode is 0.7 V and the Zener voltage is 9.10 V. If the input voltage ( $V_{in}$ ) is sine wave with an

amplitude of 15 V (as shown in the figure above), which of the following waveform qualitatively describes the output voltage ( $V_{out}$ ) across the load?

[CSIR-JUNE 2022]



#### ✤ GATE PYQ

**1.** For the rectifier circuit shown in the figure, the sinusoidal voltage  $(V_1 \text{ or } V_2)$  at the output of the transformer has a maximum value of 10 V. The load resistance  $R_L$  is  $k\Omega$ . If  $I_{\text{ave}}$  is the average current through the resistor  $R_L$  the circuit corresponds [GATE 2005]



(a) full wave rectifier with  $I_{av} = 20/\pi \text{mA}$ 

- (b) half wave rectifier with  $I_{av} = 20/\pi mA$
- (c) half wave rectifier with  $I_{av} = 10/\pi mA$

(d) full wave rectifier with  $I_{av} = 10/\pi mA$ 

**2.** A sinusoidal input voltage  $v_{in}$  of frequency  $\omega$  is fed to the circuit shown in the figure, where  $C_1 \gg C_2$ . If  $v_m$  is the peak value of the input voltage, then output voltage ( $v_{out}$ ) is





(a) 2*v*<sub>m</sub>

(b)  $2v_0 \sin \omega t$ 

(c) 
$$\sqrt{2}v_m$$
 (d)  $\frac{v_m}{2}\sin\omega t$ 

**3.** When an input voltage  $V_i$ , of the form shown, is applied to the circuit given below, the output voltage  $V_0$  is of the form **[GATE 2007]** 





(c) 6.36 V



**5.** A voltage regulator has ripple rejection of -50 dB. If input ripple is 1mV, what is the output ripple voltage in  $\mu V$ ? The answer should be up to two decimal places\_\_\_\_\_.

[GATE 2013]

6. In the figure given below, the input to the primary of the transformer is a voltage varying sinusoidally with time. The resistor *R* is connected to the centre tap of the secondary. Which one of the following plots represents the voltage across the resistor R as a function of time? [GATE 2017]





7. An input voltage in the form of a square wave of frequency 1kHz is given to a circuit, which results in the output shown schematically below. Which one of the following options is the CORRECT representation of the circuit?



#### ✤ JEST PYQ

(a)

(c)

**1.** In the following silicon diode circuit ( $V_B = 0.7$  V), determine the output waveform ( $V_{out}$ ) for the given input wave.





[JEST 2017]





#### TIFR PYQ

**1.** Consider the following circuit.



Which of the graphs given below is a correct representation of  $V_{out}$ ? [TIFR 2014]





- 2. Consider a sawtooth waveform which rises linearly from 0 Volt to 1 Volt in 10 ns and then decays linearly to 0 V over a period of 100 ns. Find the r.m.s. voltage in units of milliVolt? [TIFR 2016]
- **3.** A current source produces a square wave *I*(*t*) of 1.0 V peak-to-peak voltage and is used to drive the RC circuit shown below.

Which of the following represents the correct voltage across the capacitor C?

[TIFR 2017]



**4.** The signal shown on the left side of the figure below is fed into the circuit shown on the right side.



If the signal has time period  $\tau_S$  and the circuit has a natural frequency  $\tau_{RC}$ , then, in the case when  $\tau_S \ll \tau_{RC}$ , the steady-state output will resemble [TIFR 2019]



(c)



			*	Ar	nswer k	Key			
				CSI	R-NET				
1.	а	2.	b	3.	b	4.	С	5.	а
6.	С	7.	b						
				(	GATE				
1.	а	2.	а	3.	С	4.	С	5.	3.16
6.	a	7.	а						
				J	EST				
1.	b	2.	а	3.	а	4.	а		
				TIF	FR PYQ				
1.	b	2.	577	3.	d	4.	d		

## **ANALOG ELECTRONICS: Frequency Modulation**

#### ✤ CSIR-NET PYQ

- A live music broadcast consists of a radio-wave of frequency 7MHz, amplitude-modulated by a microphone output consisting of signals with a maximum frequency of 10KHz. The spectrum of modulated output will be zero outside the frequency band [CSIR-DEC 2012]

   (a) 7.00MHz to 7.01MHz
  - (b) 6.99MHz to 7.01MHz
  - (c) 6.99MHz to 7.00MHz
  - (d) 6.995MHz to 7.005MHz
- 2. The amplitude of a carrier signal of frequency  $f_0$  is simusoidally modulated at a frequency  $f' * f_0$ . Which of the following graphs best describes its power spectrum? [CSIR-DEC 2018]





#### ✤ TIFR PYQ

1. The figure below shows a carrier frequency 4kHz being amplitude-modulated by a sine wave signal.



In order to transmit the signal (without distortion) the minimum bandwidth needed would be [TIFR 2020] (a) 8kHz (b) 2kHz

(d) 6kHz

(c) 4kHz

					_				
	🌣 Answer Key								
				CSIR-NET					
1.	b	2. 1	b						
				TIFR PYQ					
1.	b								

## **ANALOG ELECTRONICS:** Oscillatory



## **DIGITAL ELECTRONICS: Boolean Algebra**

- ✤ CSIR-NET PYQ
- **1.** The logic circuit shown in the figure below. implements the Boolean expression

[CSIR-DEC 2012]



- (a)  $y = \overline{A \cdot B}$  (b)  $y = \overline{A} \cdot \overline{B}$
- (c) y = A.B (d) y = A + B
- **2.** A 4-variable switching function is given by  $f = \Sigma(5,7,8,10,13,15) + d(0,1,2)$ , where *d* is the donot-care-condition. The minimized form of *f* in sum of products (SOP) form is

[CSIR-DEC 2013]

(a)  $\overline{A}\overline{C} + \overline{B}\overline{D}$ 

(b) 
$$AB + CD$$

(c) AD + BC (d)  $\overline{BD} + BD$ 

**3.** The truth table below gives the value Y(A, B, C), where A, B and C are binary variables.

Α	R	C.	Y
0	0	0	1
0	0	1	0
0	1	0	0
0	1	1	1
1	0	0	1
1	0	1	0
1	1	0	0
1	1	1	1

The output Y can be represented by [CSIR-DEC 2018] (a)  $Y = \overline{ABC} + \overline{ABC} + A\overline{BC} + A\overline{BC}$ (b)  $Y = \overline{ABC} + \overline{ABC} + A\overline{BC} + A\overline{BC}$ 

- (c)  $Y = \overline{A}\overline{B}C + \overline{A}BC + A\overline{B}C + ABC$
- (d)  $Y = \overline{A}\overline{B}\overline{C} + \overline{A}B\overline{C} + A\overline{B}\overline{C} + AB\overline{C}$

**4.** The logic circuit that will have the output

$$Y = (A + B)\overline{(\overline{A}(\overline{B} + \overline{C}))} + \overline{A}(B + C)$$
  
Is [CSIR-DEC 2024]



#### ✤ GATE PYQ

 Which of the given relations between the Boolean variables P and Q is NOT correct? (In the notation used here, P' denotes NOT P and Q' denotes NOT Q)

	[GATE 2003]
(a) $PQ' + PQ = P$	(b) $(PQ)' = P' + Q'$
(c) $PQ' = (P' + Q)'$	(d) $PQ' + Q = P$

2. Which one of the set of values given below does NOT satisfy the Boolean relation R = PQ' (where Q' denotes NOT Q)? [GATE 2003]
(a) P = 1, Q = 1, R = 0

(b) 
$$P = 1, Q = 1, R = 1$$

(c) 
$$P = 0, Q = 0, R = 0$$

(d) 
$$P = 0, Q = 1, R = 1$$

- **3.** The Boolean expression  $Y = \overline{ABCD} + \overline{ABCD} + \overline{ABCD} + \overline{ACD} + \overline{ABCD} + \overline{ABCD}$  reduces to [GATE 2004] (a)  $\overline{AB}$  (b) D
  - (c)  $\overline{A}$  (d)  $\overline{A}D$
- **4.** The Boolean expression:  $B(A + B) + A \cdot (\overline{B} + A)$  can be realized using minimum number of

	[GATE 2005]
(a) 1 AND gate	(b) 2 AND gates

(c) 1 OR gate (d) 2 OR gates





## **DIGITAL ELECTRONICS: Logic Gates**

#### ✤ CSIR-NET PYQ

**1.** Consider the digital circuit shown below in which the input C is always high (I).



(high)

The truth table for the circuit can be written as

Α	В	Ζ
0	0	
0	1	
1	0	
1	1	

The entries in the Z column (vertically) are [CSIR-IUNE 2011]

	LCDIK JOHE 20
(a) 1010	(b) 0100

- (d) 1011 (c) 1111
- The output 0, of the given circuit in cases I and 2. II, where Case I : A, B = 1; C, D = 0; E, F = 1 and G = 0

Case II : A, B = 0; C, D = 0; E, F = 0 and G = 1are respectively [CSIR-JUNE 2012]



(a) 1,0

(c) 0,0 (d) 1,1

Four digital outputs V, P, T and H monitor the 3. speed v, tyre pressure p, temperature t and relative humidity *h* of a car. These outputs switch from 0 to 1 when the values of the parameters exceed 85 km/hr, 2bar, 40°C and 50%, respectively. A logic circuit that is used to switch ON a lamp at the output E is shown below.



65

6. In the schematic figure given below, assume that the propagation delay of each logic gate is  $t_{gume}$ .

The propagation delay of the circuit will be maximum when the logic inputs A and B make the transition [CSIR-JUNE 2016]



 In the figures below, X and Y are one bit inputs. The circuit which corresponds to a one bit comparator is [CSIR-JUNE 2017]





- 8. Which of the following gates can be used as a parity checker? [CSIR-JUNE 2018](a) an OR gate
  - (b) a NOR gate
  - (c) an exclusive OR (XOR) gate
  - (d) an AND gate
- **9.** Let *Y* denote the output in the following logical circuit.



If  $Y = AB + \bar{C}\bar{D}$ , the gates  $G_1$  and  $G_2$  must,respectively, be**[CSIR-JUNE 2019]**(a) OR and NAND(b) NOR and OR

(d) NAND and OR

(c) AND and NAND

- **10.** The Boolean equation  $Y = \overline{ABC} + \overline{ABC} + A\overline{BC} + A\overline{BC} + A\overline{BC}$  is to be implemented using only twoinput NAND gates. The minimum number of gates required is **[CSIR-JUNE 2020]** (a) 3 (b) 4
  - (c) 5 (d) 6
- **11.** The door of an *X* ray machine room is fitted with a sensor *D* (0 is open and 1 is closed). It is also equipped with three fire sensors  $F_1$ ,  $F_2$  and  $F_3$  (each is 0 when disable and 1 when enabled).

The *X*-ray machine can operate only if the door is closed and at least 2 fire sensors are enabled. The logic circuit to ensure that the machine can be operated is **[CSIR-JUNE 2021]** 



**12.** A liquid oxygen cylinder system is fitted with a level-sensor (L) and a pressure-sensor (P), as shown in the figure below. The outputs of L and P are set to logic high (S = 1) when the measured values exceed the respective preset threshold values. The system can be shut off either by an operator by setting the input S to high, or when the level of oxygen in the tank falls below the threshold value.









#### ✤ TIFR PYQ

1. The digital electronic circuit shown below (left side) has some problem and is not performing as intended. The voltage at each pin as a function of time is shown in the adjacent figures.



The problem in the about circuit may be that

[TIFR 2011]

- (a) the Pin 6 is shorted to ground
- (b) the input inverter is shorted
- (c) the Pin 8 is clamped to +5 V
- (d) OR gate is used instead of AND gate
- **2.** Consider the circuit shown below.



Гhe minimum number o	of NAND gates required	ł
to design this circuit is	[TIFR 2012	]
(a) 6	(b) 5	

(c) 4 (d) 3

3. The circuit shown below uses only NAND gates.
Find the final output. [TIFR 2013]
(a) A XOP P

(a) A XOR B

(c) A AND B



4. A control circuit needs to be designed to save on power consumption by an air-conditioning unit *A* in a windowless room with a single door. The room is fitted with the following devices:

1. a temperature sensor *T*, which is enabled (T = 1) whenever the temperature falls below a pre-set value;

2. a humidity sensor *H*, which is enabled (H = 1) whenever the humidity falls below a certain pre-set value;

3. a sensor *D* on the door, which is triggered (D = 1) whenever the door opens.

Which of the following logical circuits will turn the air-conditioning unit off (A = 0) whenever the door is opened or when both temperature and humidity are below their pre-set values?

[TIFR 2014]



**5.** In a digital circuit for three input signals (A, B and C) the final output (Y) should be such that for inputs

А	В	С
0	0	0
0	0	1
0	1	0

the output  $(\overline{Y})$  should be low and for all other cases it should be high.

Which of the following digital circuits will give


obtained were as shown below [TIFR 2021]

three inputs *A*, *B* and *C* is:

(a) 4

[TIFR 2024]

(b) 7



## DIGITAL ELECTRONICS: Sequential CKT



7. The circuit below comprises of D-flip flops. The (d) connect Q to J input and  $\overline{Q}$  to K input output is taken from  $Q_3$ ,  $Q_2$ ,  $Q_1$  and  $Q_0$ , as shown in the figure. **10.** In the 3-bit register shown below,  $Q_1$  and  $Q_3$  are LSB MSB the least and the most significant bits of the 0 output, respectively.  $CLR \bar{Q}$ CLR  $Q_3$ CLK = +1 $Q_3$  $Q_2$  $Q_1$  $D_{2}$ D.  $D_{1}$ The binary number given by the string  $Q_3 Q_2 Q_1 Q_0$  changes for every clock pulse that is CLK applied to the CLK input. If the output is initialized at 0000, then the corresponding If  $Q_1$ ,  $Q_2$  and  $Q_3$  are set to zero initially, then the sequence of decimal numbers that repeats output after the arrival of the second falling itself, is clock (CLK) edge is **[CSIR-JUNE 2020]** [CSIR-DEC 2017] (a) 001 (b) 100 (a) 3,2,1,0 (c) 011 (d) 110 (b) 1,3,7,14,12,8 ✤ GATE PYQ (c) 1,3,7,15,12,14,0 1. A ripple counter designed with JK flip-flops provided with CLEAR(CL) input is shown in the (d) 1,3,7,15,14,12,8,0 figure. In order that this circuit functions as a MOD-12 counter, the NAND gate input  $(X_1 and$ **8.** In the following JK flip-flop circuit, J and K  $X_2$ ) should be [GATE 2006] inputs are tied together to  $+V_{cc}$ . If the input is a (a) A and C (b) A and D clock signal of frequency *f*, the frequency of the output Q is **[CSIR-JUNE 2018]** (c) B and D (d) C and D  $+V_{CC}$ 2. The registers  $Q_D$ ,  $Q_C$ ,  $Q_B$  and  $Q_A$  shown in the ٥Q figure are initially in the state 1010 Clock signal respectively. An input sequence SI = 0101 is applied. After two clock pulses, the state of the (a) f (b) 2f shift registers (in the same sequence [GATE 2007]  $Q_D Q_C Q_B Q_A$ ) is (c) 4f (d) f/20101 **9.** Consider the following circuit, consisting of an RS flip-flop and two AND gates. Which of the following connections will allow (a) 1001 (b) 0100 the entire circuit to act as a JKip-flop? [CSIR-DEC 2018] (c) 0110 (d) 1010 CLK-E **3.** In the circuit shown, the ports  $Q_1$  and  $Q_2$  are in the state  $Q_1 = 1$ ,  $Q_2 = 0$ . The circuit is now subjected to two complete clock pulses. The (a) connect Q to pin 1 and  $\overline{Q}$  to pin 2 state of these ports now becomes[GATE 2007] (b) connect Q to pin2 and  $\overline{Q}$  to pin 1

(c) connect Q to K input and  $\overline{Q}$  to I input



**4.** In the T type master slave JK flip flop is shown along with the clock and input wave forms. The  $Q_n$  output of flip flop was zero initially. Identify the correct output wave form



**5.** The minimum number of flip-flops required to construct a mod- 75 counter is.....

[GATE 2014]

6. Consider a 4-bit counter constructed out of four flip-flops. It is formed by connecting the *J* and *K* inputs to logic high and feeding the *Q* output to the clock input of the following flip-flop (see the figure). The input signal to the counter is a series of square pulses and the change of state is triggered by the falling edge. At time  $t = t_0$  the outputs are in logic low state ( $Q_0 = Q_1 = Q_2 = Q_3 = 0$ ). Then at  $t = t_1$ , the logic state of the outputs is



(b)
$$Q_0 = 0, Q_1 = 0, Q_2 = 0$$
 and  $Q_3 = 1$ 

$$(c)Q_0 = 1, Q_1 = 0, Q_2 = 1 \text{ and } Q_3 = 0$$

$$(d)Q_0 = 0, Q_1 = 1, Q_2 = 1 \text{ and } Q_3 = 1$$

🛠 Answer Key					
CSIR-NET					
1.	b	2. d	3. b	4. d	5. d
6.	d	7. d	8. d	9. b	10. c
GATE					
1.	d	2. a	3. c	4. a	5. 7
6.	b				



## **DIGITAL ELECTRONICS:** Combinational Circuits





## **DIGITAL ELECTRONICS: Number System**

